

# Sonic Fast Recovery Diode

$V_{RRM}$  = 1800 V  
 $I_{FAV}$  = 40 A  
 $t_{rr}$  = 300 ns

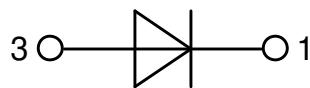
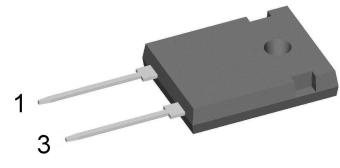
High Performance Fast Recovery Diode

Low Loss and Soft Recovery

Single Diode

Part number

**DH40-18A**



## Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

## Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

## Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

## Disclaimer Notice

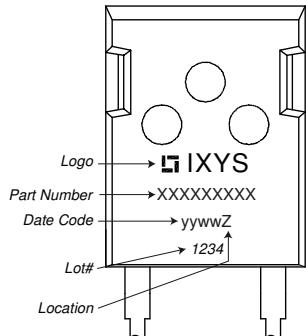
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**Fast Diode**

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
$V_{RSM}$	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ\text{C}$			1800	V
$V_{RRM}$	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ\text{C}$			1800	V
$I_R$	reverse current, drain current	$V_R = 1800 \text{ V}$ $V_R = 1800 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		100 1	$\mu\text{A}$ mA
$V_F$	forward voltage drop	$I_F = 40 \text{ A}$ $I_F = 80 \text{ A}$ $I_F = 40 \text{ A}$ $I_F = 80 \text{ A}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		2.06 2.56 2.08 2.79	V V V V
$I_{FAV}$	average forward current	$T_C = 100^\circ\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 150^\circ\text{C}$		40	A
$V_{F0}$ $r_F$	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ\text{C}$		1.38 17.5	V $\text{m}\Omega$
$R_{thJC}$	thermal resistance junction to case				0.45	K/W
$R_{thCH}$	thermal resistance case to heatsink			0.3		K/W
$P_{tot}$	total power dissipation		$T_C = 25^\circ\text{C}$		280	W
$I_{FSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}; V_R = 0 \text{ V}$	$T_{VJ} = 45^\circ\text{C}$		400	A
$C_J$	junction capacitance	$V_R = 900 \text{ V}$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$	19		pF
$I_{RM}$	max. reverse recovery current		$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	50 60		A A
$t_{rr}$	reverse recovery time	$I_F = 60 \text{ A}; V_R = 900 \text{ V}$ $-di_F/dt = 750 \text{ A}/\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	300 550		ns ns

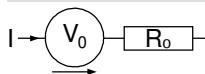
**Package TO-247**

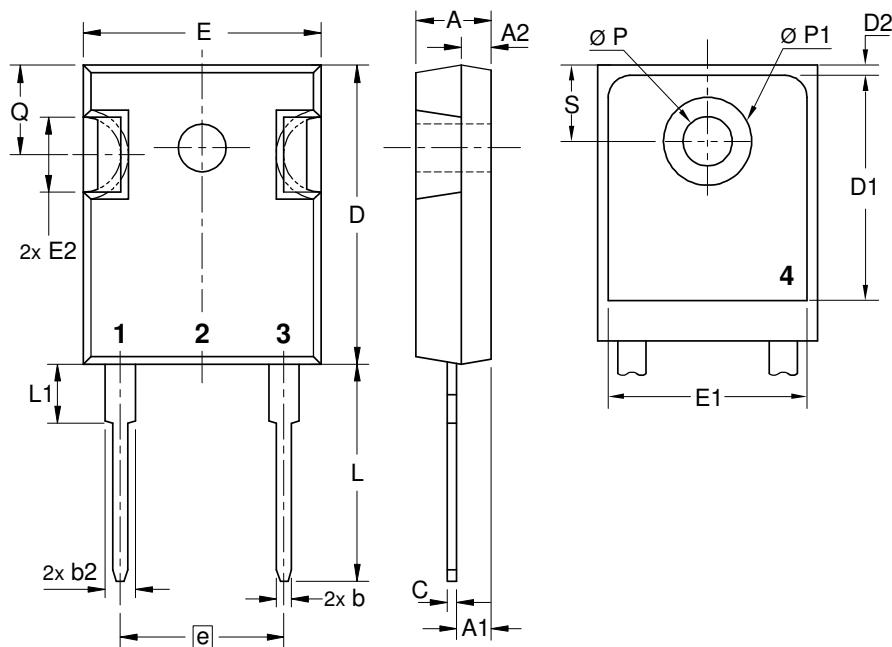
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			70	A
$T_{VJ}$	virtual junction temperature		-55		150	°C
$T_{op}$	operation temperature		-55		125	°C
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				6		g
$M_d$	mounting torque		0.8		1.2	Nm
$F_c$	mounting force with clip		20		120	N

**Product Marking**


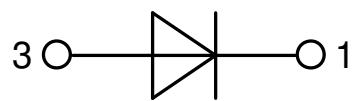
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DH40-18A	DH40-18A	Tube	30	499765

**Equivalent Circuits for Simulation**
\* on die level
 $T_{VJ} = 150^\circ\text{C}$ 

	<b>Fast Diode</b>	
$V_{0\max}$	threshold voltage	1.38
$R_{0\max}$	slope resistance *	14.5

**Outlines TO-247**


Sym.	Inches min. max.	Millimeter min. max.
A	0.185 0.209	4.70 5.30
A1	0.087 0.102	2.21 2.59
A2	0.059 0.098	1.50 2.49
D	0.819 0.845	20.79 21.45
E	0.610 0.640	15.48 16.24
E2	0.170 0.216	4.31 5.48
e	0.430 BSC	10.92 BSC
L	0.780 0.800	19.80 20.30
L1	- 0.177	- 4.49
$\varnothing$ P	0.140 0.144	3.55 3.65
Q	0.212 0.244	5.38 6.19
S	0.242 BSC	6.14 BSC
b	0.039 0.055	0.99 1.40
b2	0.065 0.094	1.65 2.39
b4	0.102 0.135	2.59 3.43
c	0.015 0.035	0.38 0.89
D1	0.515 -	13.07 -
D2	0.020 0.053	0.51 1.35
E1	0.530 -	13.45 -
$\varnothing$ P1	- 0.29	- 7.39



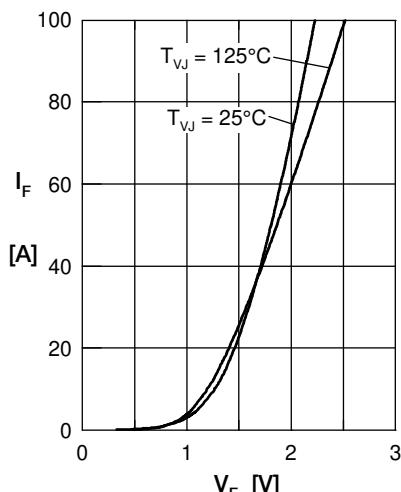
**Fast Diode**


Fig. 1 Forward current  
 $I_F$  versus  $V_F$

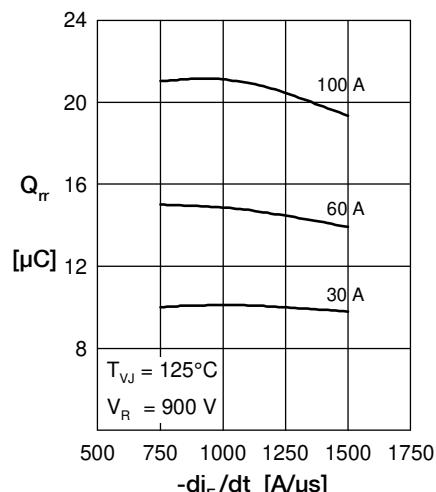


Fig. 2 Typ. reverse recovery charge  
 $Q_{rr}$  versus  $-di_F/dt$

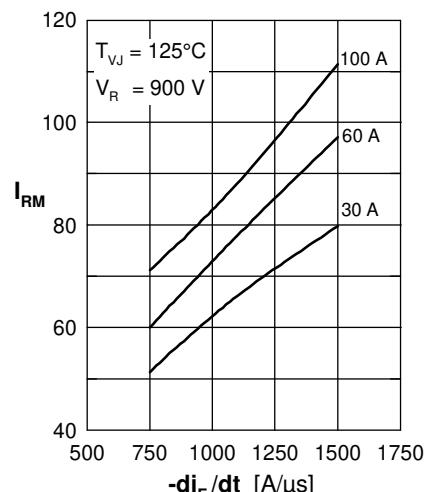


Fig. 3 Typ. peak reverse current  
 $I_{RM}$  versus  $-di_F/dt$

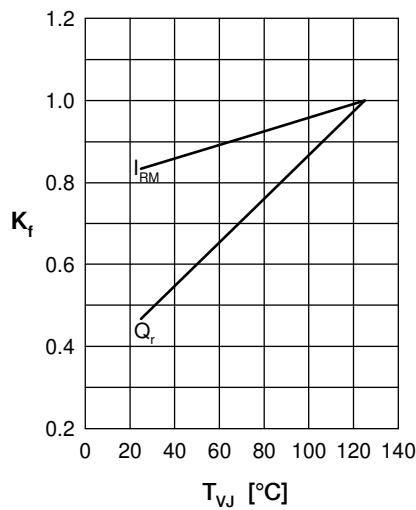


Fig. 4 Dyn. parameters  
 $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

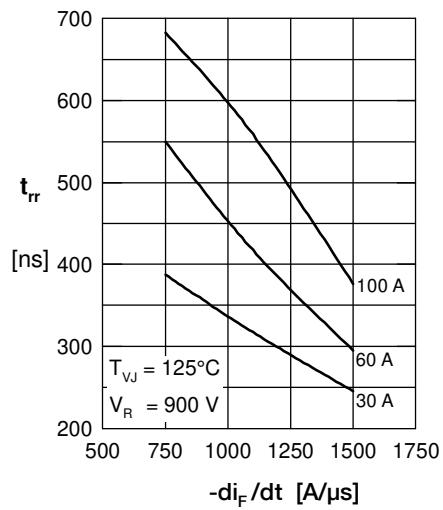


Fig. 5 Typ. recovery time  
 $t_{rr}$  versus  $-di_F/dt$

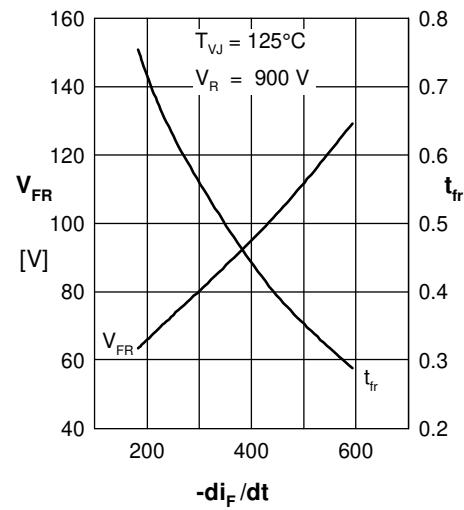


Fig. 6 Typ. peak forward voltage  
 $V_{FR}$  and  $t_{tr}$  versus  $di_F/dt$

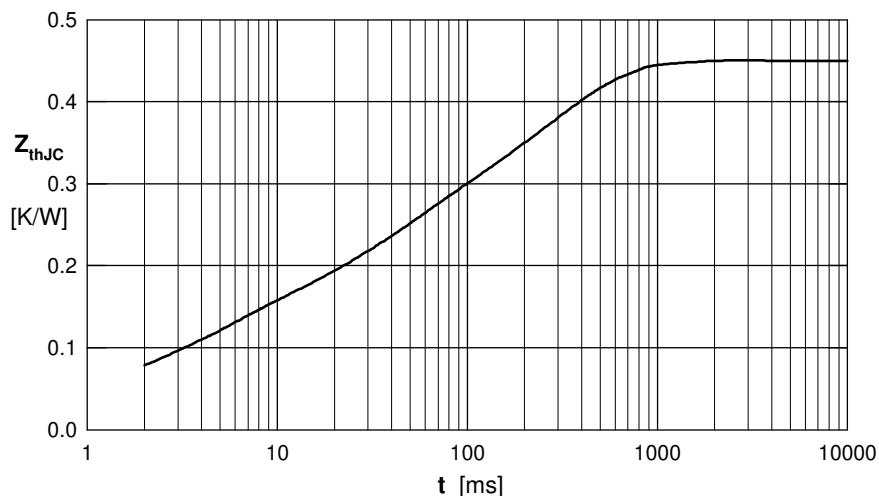


Fig. 7 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{th}$ (K/W)	$t_i$ (s)
1	0.033	0.0006
2	0.095	0.0039
3	1.114	0.0330
4	0.208	0.2720